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## Diode-pumped erbium-ytterbium-glass laser passively Q-switched with a PbS semiconductor quantum-dot doped glass

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Due to a technical oversight, Fig. 3 was lost from the article and Fig. 2 was printed twice (only in the printed version). Figures 2 and 3 have been produced in their right form here.

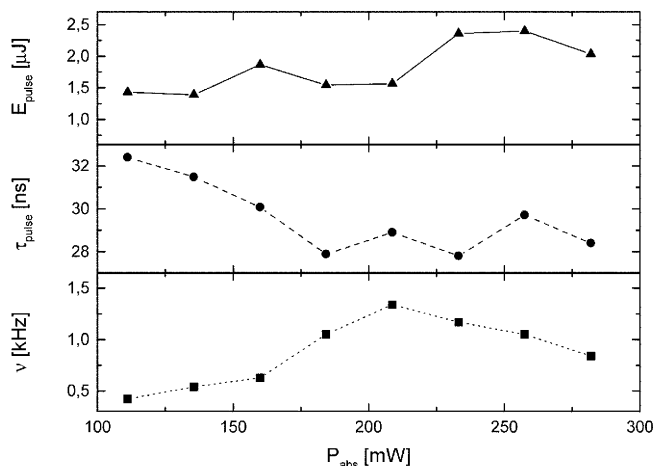


FIGURE 2 Pulse energy, pulse width and repetition rate for phosphate glass with 300- $\mu\text{m}$ -thick absorber

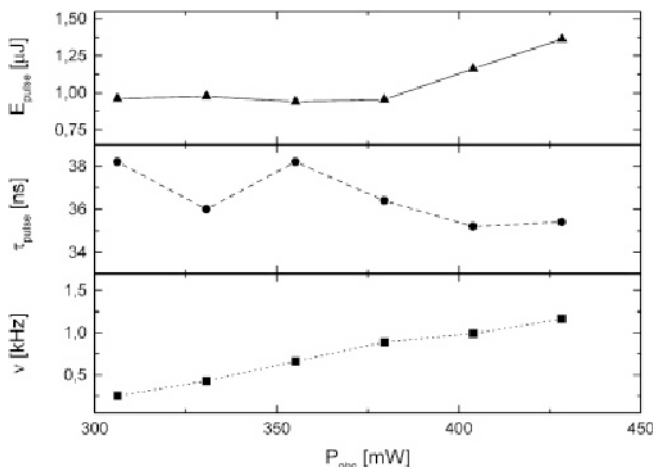


FIGURE 3 Pulse energy, pulse width and repetition rate for fluoride phosphate glass with 300- $\mu\text{m}$ -thick absorber